A	2021.10.26	All	AOS-AON6298		

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Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Continuous Drain Current		I_D	46	A
Pulsed Drain Current		I_{DM}	184	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		$P_D(T_c=25℃)$	78	W
Avalanche energy(L=0.5mH)		E_{AS}	24.5	mJ
Avalanche Current(L=0.5mH)		I_{AS}	7.0	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	℃
Maximum Junction-to-Ambient	t ≤ 10s	$R_{\theta JA}$	17	/ W
	Steady-State		55	
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1.6	

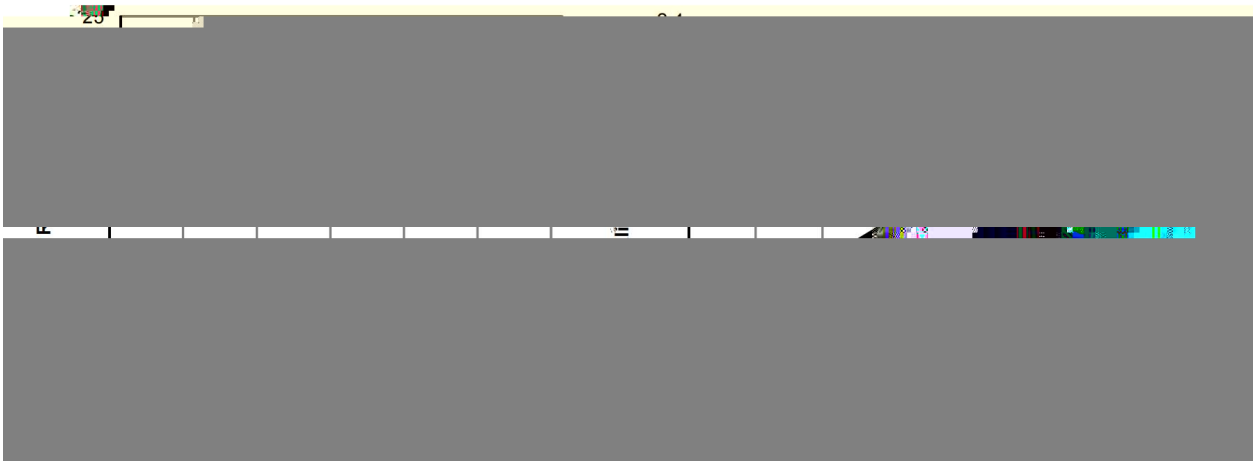
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250uA, V_{GS}=0V	100	109		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}= ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	1.7	2.5	V

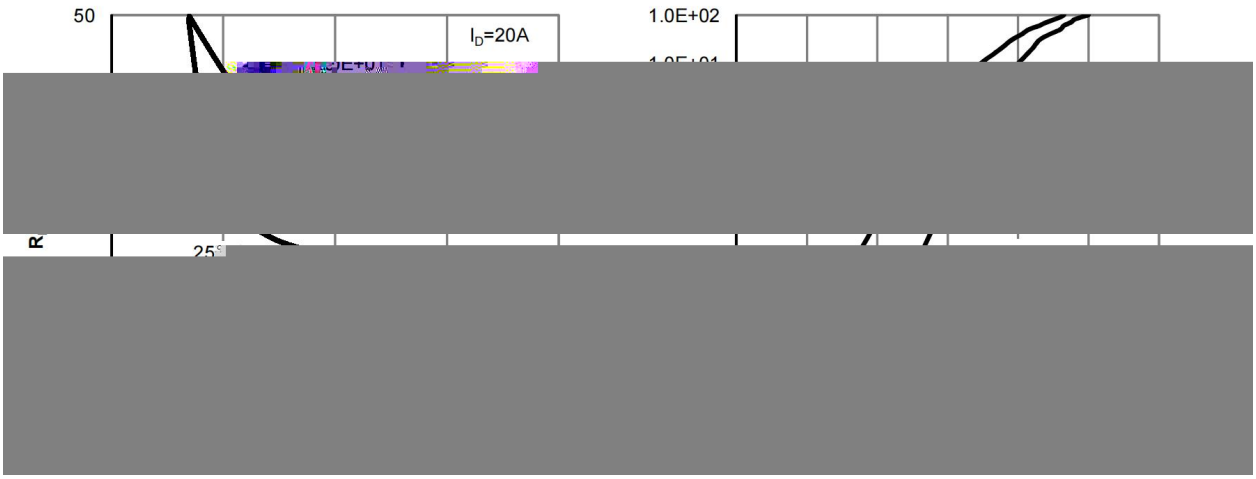
Static Drain-Source On-Resistance Rin

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

/ Electrical Characteristic Curve

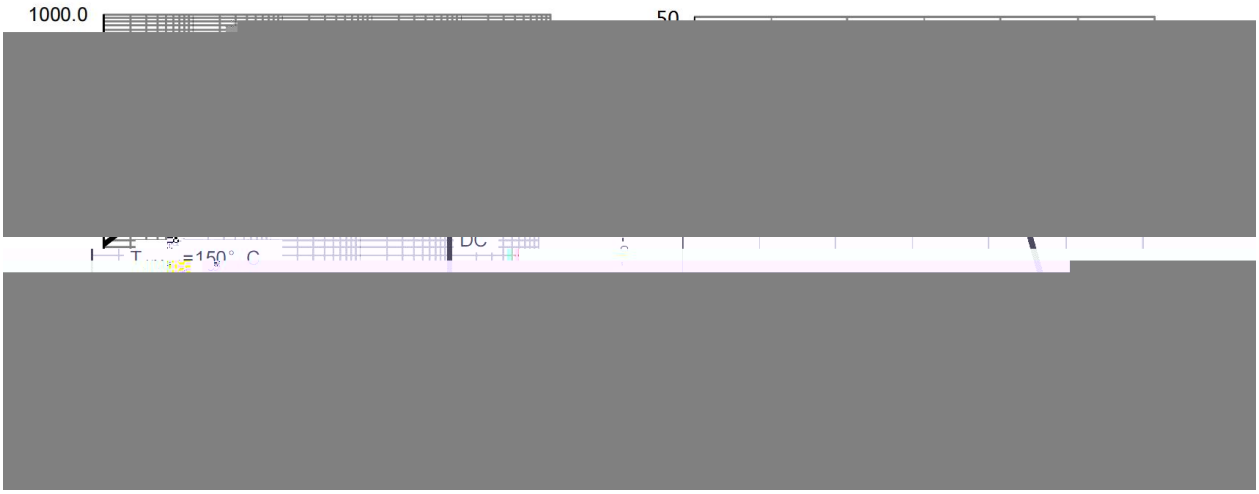


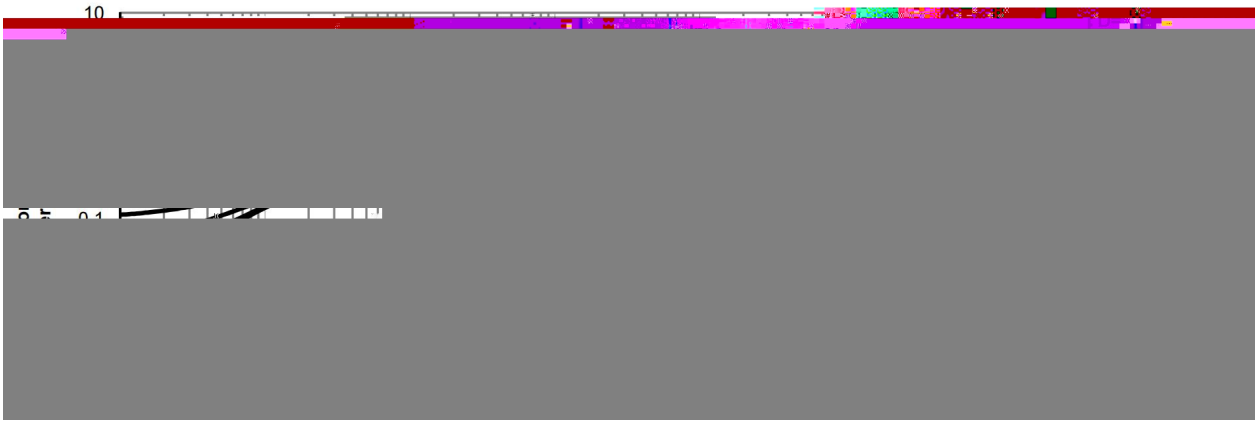




/ Electrical Characteristic Curve







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( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1 150 180